

Application No. 10/623,351
Amendment "A" dated October 12, 2004
Reply to Office Action mailed May 14, 2004

AMENDMENTS TO THE CLAIMS

The listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

1. **(Withdrawn)** A wafer receiving apparatus comprising:
a body having a pocket shaped to receive a wafer, the pocket having a depth and an area which correspond to a wafer of a first size.
2. **(Withdrawn)** The wafer receiving apparatus of claim 1 wherein the body further includes at least one channel connected to the pocket, wherein the channel is adapted to allow a vacuum force to be applied to a wafer placed in the pocket.
3. **(Withdrawn)** The wafer receiving apparatus of claim 1 wherein the body is shaped to correspond to a wafer of a second size that is larger than the first size.
4. **(Withdrawn)** The wafer receiving apparatus of claim 1 wherein the body includes a face that surrounds the pocket, wherein the face is adapted to allow easy removal of photoresist.
5. **(Cancelled)**
6. **(Currently Amended)** The method of claim 5 10 wherein the depth of the recessed portion is selected to flatten the photoresist profile on the wafer.
7. **(Original)** The method of claim 6 wherein the depth of the recessed portion is substantially equal to the thickness of the wafer.

Application No. 10/623,351
Amendment "A" dated October 12, 2004
Reply to Office Action mailed May 14, 2004

8. **(Currently Amended)** The method of claim 5 10 wherein the wafer receiving apparatus further includes a channel coupled to the recessed portion, the channel adapted to allow a vacuum force to be applied within the recessed portion.

9. **(Original)** The method of claim 8 further comprising:

applying a vacuum force via the channel after the wafer is placed, the vacuum force being applied such that the wafer is held in place in the recessed portion.

10. **(Currently Amended)** The method of claim 5 A method of preparing a wafer for a fabrication process, the method comprising:

providing a wafer receiving apparatus for receiving a wafer of a first size, the wafer receiving apparatus including a recessed portion having a depth;

placing a wafer of the first size in the recessed portion of the wafer receiving apparatus;

applying photoresist to the wafer;

spinning the wafer and the wafer receiving apparatus while the wafer is placed in the recessed portion of the wafer receiving apparatus; and

wherein the wafer receiving apparatus further includes a circumferential groove in the recessed portion, wherein the method further comprises:

allowing a fluid to enter the circumferential groove; and

causing the fluid in the circumferential groove to expand and release the wafer from the pocket.

11. **(Currently Amended)** The method of claim 5 10 wherein the spinning step is performed such that the spinning distributes the photoresist onto both the wafer and the wafer receiving apparatus.

12. **(Cancelled)**

Application No. 10/623,351
Amendment "A" dated October 12, 2004
Reply to Office Action mailed May 14, 2004

13. **(Currently Amended)** The method of claim 12 A method of reducing edge bead thickness while applying photoresist to a wafer comprising:
providing a wafer receiving apparatus for receiving a wafer of a first size, the wafer receiving apparatus including a pocket having a depth, wherein the depth is chosen to correspond to a wafer of the first size;
placing a wafer of the first size in the pocket of the wafer receiving apparatus;
applying photoresist to the wafer;
spinning the wafer and the wafer receiving apparatus while the wafer is placed in the pocket to create a photoresist layer of a desired thickness; and
wherein the wafer receiving apparatus is sized to be compatible with machines adapted for use with wafers of a second size larger than the first size.

14. **(Currently Amended)** The method of claim 12 13 wherein the depth is greater than the thickness of the wafer.

15. **(Currently Amended)** The method of claim 14 13 wherein the depth is less than the thickness of the wafer plus the thickness of the desired photoresist layer.

16. **(Currently Amended)** The method of claim 12 13 wherein the depth is substantially equal to the thickness of the wafer.

17. **(Currently Amended)** The method of claim 12 13 wherein the first size is the size of a three inch wafer, and the second size is the size of a four inch wafer.

18. **(Currently Amended)** The method of claim 12 13 further comprising securing the wafer in the pocket.

Application No. 10/623,351
Amendment "A" dated October 12, 2004
Reply to Office Action mailed May 14, 2004

19. **(Currently Amended)** The method of claim 12 13 wherein the wafer receiving apparatus further includes a channel coupled to the recessed portion, the channel adapted to allow a vacuum force to be applied within the recessed portion and wherein the step of securing the wafer in the pocket includes:

applying a vacuum force via the channel after the wafer is placed, the vacuum force being applied such that the wafer is held in place in the recessed portion.

20. **(Currently Amended)** The method of claim 12 13 wherein the wafer receiving apparatus further includes a circumferential groove in the recessed portion, wherein the method further comprises:

allowing a fluid to enter the circumferential groove; and
causing the fluid in the circumferential groove to expand and release the wafer from the pocket.

21. **(New)** A method of reducing edge bead thickness while applying photoresist to a wafer comprising:

providing a wafer receiving apparatus for receiving a wafer of a first size, the wafer receiving apparatus including a pocket having a depth, wherein the depth is chosen to correspond to a wafer of the first size;

placing a wafer of the first size in the pocket of the wafer receiving apparatus;
applying photoresist to the wafer;
spinning the wafer and the wafer receiving apparatus while the wafer is placed in the pocket to create a photoresist layer of a desired thickness; and
wherein the depth is less than the thickness of the wafer plus the thickness of the desired photoresist layer.

22. **(New)** A method of reducing edge bead thickness while applying photoresist to a wafer comprising:

Application No. 10/623,351
Amendment "A" dated October 12, 2004
Reply to Office Action mailed May 14, 2004

providing a wafer receiving apparatus for receiving a wafer, the wafer receiving apparatus being sized to be compatible with machines adapted for use with wafers of a second size larger than wafers of a first size, the wafer receiving apparatus including a pocket having a depth, wherein the depth is chosen to correspond to a wafer of the first size;

placing a wafer of the first size in the pocket of the wafer receiving apparatus;

applying photoresist to the wafer;

spinning the wafer and the wafer receiving apparatus while the wafer is placed in the pocket to create a photoresist layer of a desired thickness; and

wherein the first size is the size of a three inch wafer, and the second size is the size of a four inch wafer.

23. (New) A method of reducing edge bead thickness while applying photoresist to a wafer comprising:

providing a wafer receiving apparatus for receiving a wafer of a first size, the wafer receiving apparatus including a pocket having a depth, wherein the depth is chosen to correspond to a wafer of the first size;

placing a wafer of the first size in the pocket of the wafer receiving apparatus;

applying photoresist to the wafer;

spinning the wafer and the wafer receiving apparatus while the wafer is placed in the pocket to create a photoresist layer of a desired thickness; and

wherein the wafer receiving apparatus further includes a circumferential groove in the recessed portion, wherein the method further comprises:

allowing a fluid to enter the circumferential groove; and

causing the fluid in the circumferential groove to expand and release the wafer from the pocket.